



2018 IEDM Conference Theme
Device Breakthroughs from
Quantum to 5G and Beyond



2018 IEEE International Electron Devices Meeting

December 1st - 5th, 2018

Hilton San Francisco Union Square
San Francisco, California

Focused Call for Papers

IEDM is pleased to announce increased technical focus in the area of:

Power Devices

Topics

Papers are solicited in the following themes of interest:

- Si, GaN and SiC power devices
- Methods and designs for reduced dynamic R_{on} in power switches
- Device integration
- Fundamental studies leading to breakthrough in dielectric, thermal management, reliability, doping etc.

New or trending areas include:

- High Voltage SiC MOSFETs
- GaN Power devices
- Novel superjunction devices
- Ultra-widebandgap devices (Diamond, Ga_2O_3 , AlN etc.)

Streamlined Paper Submission

Submission deadline: August 1st
Single submission of final,
four-page paper

For More Information

IEDM Online: ieee-iedm.org

Social Networks: ieee-iedm.org/social-media

